

256 K × 16 Static RAM

Features

- Temperature ranges
 - □ Commercial: 0 °C to 70 °C
 - □ Industrial: -40 °C to 85 °C
 - □ Automotive-A: -40 °C to 85 °C
- High speed
 - $\Box t_{AA} = 15 \text{ ns}$
- Low active power
 - □ 1540 mW (max.)
- Low CMOS standby power (L version)

 □ 2.75 mW (max.)
- 2.0 V data retention (400 µW at 2.0 V retention)
- Automatic power-down when deselected
- TTL-compatible inputs and outputs
- Easy memory expansion with CE and OE features
- Available in Pb-free and non Pb-free 44-pin TSOP II and molded 44-pin (400-Mil) SOJ packages

Functional Description

The CY7C1041BN is a high-performance CMOS static RAM organized as 262,144 words by 16 bits.

Writing to the device is accomplished by taking Chip Enable $\overline{(CE)}$ and Write Enable $\overline{(WE)}$ inputs LOW. If Byte Low Enable $\overline{(BLE)}$ is LOW, then data from I/O pins $\overline{(I/O_0)}$ through $\overline{I/O_7}$, is written into the location specified on the address pins $\overline{(A_0)}$ through $\overline{A_{17}}$. If Byte High Enable $\overline{(BHE)}$ is LOW, then data from I/O pins $\overline{(I/O_8)}$ through $\overline{I/O_{15}}$ is written into the location specified on the address pins $\overline{(A_0)}$ through $\overline{A_{17}}$.

Reading from the device is accomplished by taking Chip Enable (CE) and Output Enable (OE) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins will appear on I/O₀ to I/O₇. If Byte High Enable (BHE) is LOW, then data from memory will appear on I/O₈ to I/O₁₅. See the truth table at the back of this data sheet for a complete description of read and write modes.

The input/output pins (I/O $_0$ through I/O $_{15}$) are placed in a high-impedance state when the device is deselected ($\overline{\text{CE}}$ HIGH), the outputs are disabled ($\overline{\text{OE}}$ HIGH), the BHE and BLE are disabled (BHE, BLE HIGH), or during a write operation ($\overline{\text{CE}}$ LOW, and $\overline{\text{WE}}$ LOW).

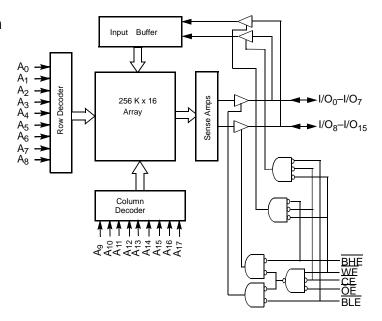
The CY7C1041BN is available in a standard 44-pin 400-mil-wide body width SOJ and 44-pin TSOP II package with center power and ground (revolutionary) pinout.

Selection Guide

Description		-15	-20	Unit
Maximum access time		15	20	ns
Maximum operating current	Commercial	190	170	mA
	Industrial	210	190	_
	Automotive-A	_	190	_
Maximum CMOS standby current	Commercial	3	3	mA
Commercial L		0.5	0.5	
	Industrial	6	6	
	Automotive-A	_	6	



Logic Block Diagram



CY7C1041BN



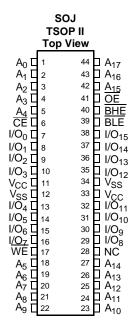
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Pin Configuration





Maximum Ratings

(Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.)

Operating Range

Range	Ambient Temperature ^[2]	V _{CC}
Commercial	0 °C to +70 °C	5 V ± 0.5
Industrial	-40 °C to +85 °C	
Automotive-A	−40 °C to +85 °C	

Electrical Characteristics Over the Operating Range

Davamatar	Description	Test Conditions		-15		-20		Unit
Parameter	Description	lest Condition	S	Min	Max	Min	Max	Unit
V _{OH}	Output HIGH voltage	$V_{CC} = Min, I_{OH} = -4.0 \text{ mA}$		2.4	_	2.4	_	V
V _{OL}	Output LOW voltage	$V_{CC} = Min, I_{OL} = 8.0 \text{ mA}$		_	0.4	_	0.4	V
V _{IH}	Input HIGH voltage	-		2.2	V _{CC} + 0.5	2.2	$V_{CC} + 0.5$	V
V _{IL}	Input LOW voltage ^[1]	-		-0.5	0.8	-0.5	0.8	V
I _{IX}	Input load current	$GND \le V_1 \le V_{CC}$		-1	+1	-1	+1	μA
I _{OZ}	Output leakage current	$GND \le V_{OUT} \le V_{CC}$, Output	GND ≤ V _{OUT} ≤ V _{CC} , Output Disabled			-1	+1	μA
I _{CC}	V _{CC} operating supply	$V_{CC} = Max$,	Comm'l	_	190	-	170	mA
	current	$f = f_{MAX} = 1/t_{RC}$	Ind'I	_	210	-	190	mA
			Auto-A	_	_	_	190	mA
I _{SB1}	Automatic CE Power-down current—TTL inputs	$\begin{aligned} &\text{Max V}_{\text{CC}}, \overline{\text{CE}} \geq \text{V}_{\text{IH}}, \text{V}_{\text{IN}} \geq \text{V}_{\text{IH}} \text{ or} \\ &\text{V}_{\text{IN}} \leq \text{V}_{\text{IL}}, \text{f} = \text{f}_{\text{MAX}} \end{aligned}$		_	40	-	40	mA
I _{SB2}	Automatic CE	Max V_{CC} , $\overline{CE} \ge V_{CC} - 0.3 \text{ V}$,	Comm'l	_	3	-	3	mA
	power-down current —CMOS inputs	$V_{IN} \ge V_{CC} - 0.3 \text{ V},$ or $V_{IN} \le 0.3 \text{ V}, f = 0$	Comm'l L	_	0.5	_	0.5	mA
			Ind'I	_	6	_	6	mA
			Auto-A	_		_	6	mA

Notes

^{1.} $V_{\rm IL}$ (min.) = -2.0 V for pulse durations of less than 20 ns.

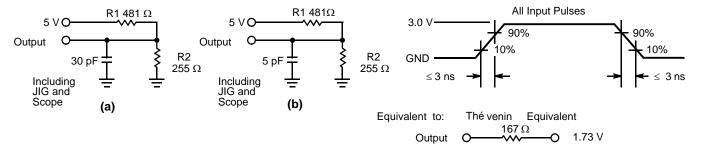
^{2.} T_A is the case temperature.



Capacitance

Parameter ^[3]	Description	Test Conditions	Max	Unit
C _{IN}	Input capacitance	$T_A = 25$ °C, f = 1 MHz,	8	pF
C _{OUT}	I/O capacitance	$V_{CC} = 5.0 \text{ V}$	8	pF

AC Test Loads and Waveforms



Switching Characteristics^[4] Over the Operating Range

Parameter	Description	-	15	-20		Unit	
Parameter	Description	Min	Max	Min	Max	Unit	
Read Cycle	·						
t _{power} V _{CC} (typical) to the First Access ^[5]		1	_	1	_	μS	
t _{RC}	Read Cycle Time	15	_	20	_	ns	
t _{AA}	Address to Data Valid	_	15		20	ns	
t _{OHA}	Data Hold from Address Change	3	_	3	_	ns	
t _{ACE}	CE LOW to Data Valid	_	15	_	20	ns	
t _{DOE}	OE LOW to Data Valid	_	7	_	8	ns	
t _{LZOE}	OE LOW to Low Z	0	_	0	_	ns	
t _{HZOE}	OE HIGH to High Z ^[6, 7]	_	7		8	ns	
t _{LZCE}	CE LOW to Low Z ^[7]	3	_	3	_	ns	
t _{HZCE}	CE HIGH to High Z ^[6, 7]	_	7		8	ns	
t _{PU}	CE LOW to Power-Up	0	_	0	_	ns	
t _{PD}	CE HIGH to Power-Down	_	15	_	20	ns	
t _{DBE}	Byte Enable to Data Valid	_	7	-	8	ns	
t _{LZBE}	Byte Enable to Low Z	0	-	0	_	ns	
t _{HZBE}	Byte Disable to High Z	_	7	_	8	ns	

Notes

- Tested initially and after any design or process changes that may affect these parameters.
 Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
 This part has a voltage regulator which steps down the voltage from 5 V to 3.3 V internally. t_{power} time has to be provided initially before a read/write operation is started.
 t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
 At any given temperature and voltage condition, t_{HZCE} is less than t_{LZOE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.



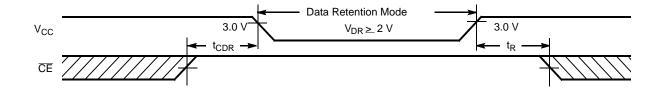
Switching Characteristics^[4] Over the Operating Range (continued)

Parameter	Description	_	15	-20		l lmit
	Description	Min	Max	Min	Max	Unit
Write Cycle ^[11, 12]	2)					
t _{WC}	Write Cycle Time	15	_	20	-	ns
t _{SCE}	CE LOW to Write End	12	_	13	-	ns
t _{AW}	Address Set-Up to Write End	12	_	13	-	ns
t _{HA}	Address Hold from Write End	0	_	0	-	ns
t _{SA}	Address Set-Up to Write Start	0	_	0	-	ns
t _{PWE}	WE Pulse Width	12	_	13	-	ns
t _{SD}	Data Set-Up to Write End	8	_	9	-	ns
t _{HD}	Data Hold from Write End	0	_	0	-	ns
t _{LZWE}	WE HIGH to Low Z ^[10]	3	_	3	-	ns
t _{HZWE}	WE LOW to High Z ^[9, 10]	_	7	-	8	ns
t _{BW}	Byte Enable to End of Write	12	_	13	_	ns

Data Retention Characteristics Over the Operating Range (L version only)

Parameter	Description	Conditions ^[14]	Min	Max	Unit
V_{DR}	V _{CC} for Data Retention	_	2.0	_	V
I _{CCDR}	Data Retention Current	$V_{CC} = V_{DR} = 2.0 \text{ V},$ $CE \ge V_{CC} - 0.3 \text{ V},$	_	200	μΑ
t _{CDR} ^[8]	Chip Deselect to Data Retention Time	$CE \ge V_{CC} - 0.3 \text{ V},$ $V_{IN} \ge V_{CC} - 0.3 \text{ V or } V_{IN} \le 0.3 \text{ V}$	0	_	ns
t _R ^[13]	Operation Recovery Time		t _{RC}	_	ns

Data Retention Waveform

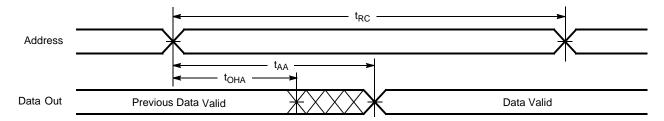


- 8. Tested initially and after any design or process changes that may affect these parameters.
 9. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
 10. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZWE} for any given device.
 11. The internal write time of the memory is defined by the overlap of CE LOW, and WE LOW. CE and WE must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data ser-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
- 12. The minimum write cycle time for Write Cycle no. 3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.
- 13. $t_r \le 3$ ns for the -15 speed. $t_r \le 5$ ns for the -20 and slower speeds.
- 14. No input may exceed $V_{CC} + 0.5 \text{ V}$.

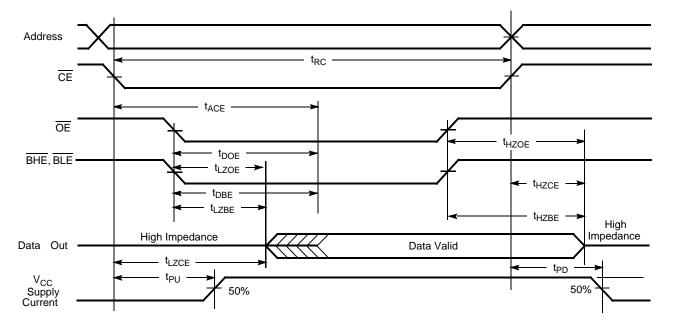


Switching Waveforms

Read Cycle No. 1^[15, 16]



Read Cycle No. 2 (OE Controlled)[16, 17]



Notes

^{15. &}lt;u>Device</u> is continuously selected. <u>OE</u>, <u>CE</u>, <u>BHE</u>, and/or <u>BHE</u> = V_{IL}.

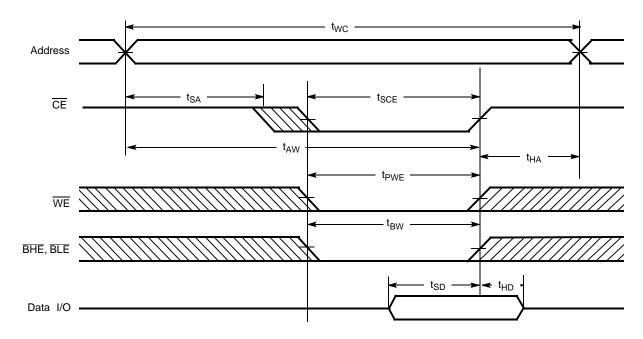
^{16.} WE is HIGH for read cycle.

^{17.} Address valid prior to or coincident with $\overline{\text{CE}}$ transition LOW.

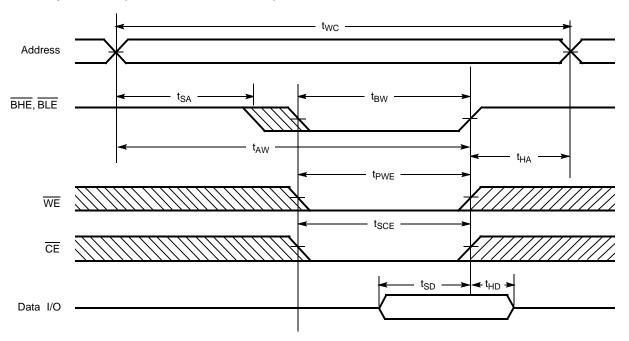


Switching Waveforms (continued)

Write Cycle No. 1 (CE Controlled)[18, 19]



Write Cycle No. 2 (BLE or BHE Controlled)



Notes

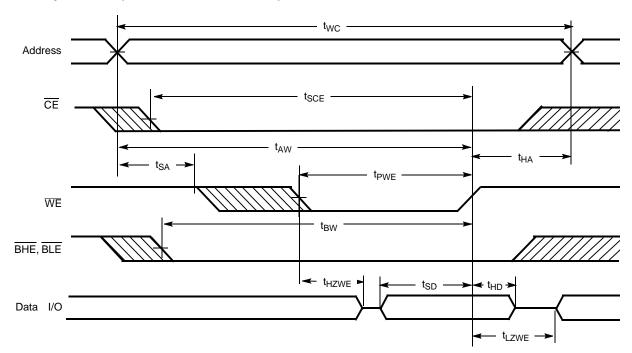
18. Data I/O is high impedance if \overline{OE} or \overline{BHE} and/or \overline{BLE} = V_{IH} .

19. If \overline{CE} goes HIGH simultaneously with \overline{WE} going HIGH, the output remains in a high-impedance state.



Switching Waveforms (continued)

Write Cycle No. 3 (WE Controlled, OE LOW)



Truth Table

CE	OE	WE	BLE	BHE	I/O ₀ –I/O ₇	I/O ₈ –I/O ₁₅	Mode	Power
Н	Χ	Χ	Χ	Х	High Z	High Z	Power down	Standby (I _{SB})
L	L	Н	L	L	Data out	Data out	Read All bits	Active (I _{CC})
L	L	Н	L	Н	Data out	High Z	Read Lower bits only	Active (I _{CC})
L	L	Н	Н	L	High Z	Data out	Read Upper bits only	Active (I _{CC})
L	Χ	L	L	L	Data in	Data in	Write All bits	Active (I _{CC})
L	Χ	L	L	Н	Data in	High Z	Write Lower bits only	Active (I _{CC})
L	Х	L	Н	L	High Z	Data in	Write Upper bits only	Active (I _{CC})
L	Н	Н	Х	Х	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})

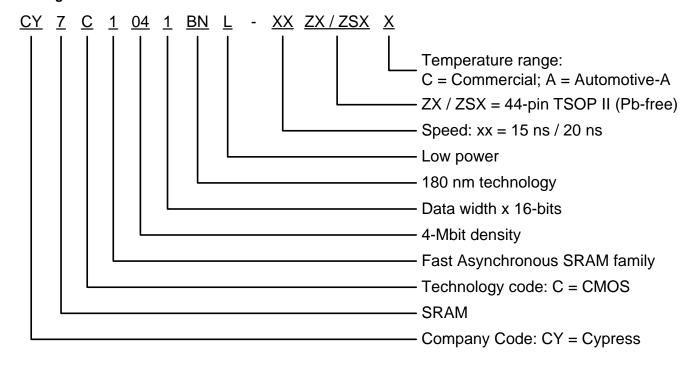


Ordering Information

Cypress offers other versions of this type of product in many different configurations and features. The following table contains only the list of parts that are currently available. For a complete listing of all options, visit the Cypress website at http://www.cypress.com/products or contact your local sales representative. Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives and distributors. To find the office closest to you, visit us at http://www.cypress.com/go/datasheet/offices.

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C1041BNL-15ZXC	51-85087	44-pin TSOP Type II (Pb-free)	Commercial
20	CY7C1041BN-20ZSXA		44-pin TSOP Type II	Automotive-A

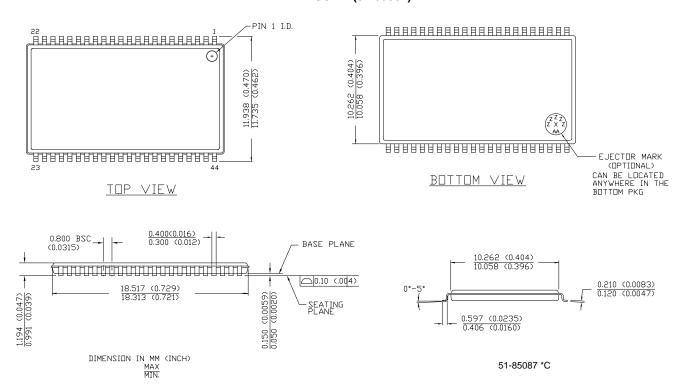
Ordering Code Definitions





Package Diagrams

44-Pin TSOP II (51-85087)



Acronyms

Acronym	Description
BHE	Byte high enable
BLE Byte low enable	
CE Chip enable	
CMOS	Complementary metal oxide semiconductor
I/O	Input/output
OE	Output enable
SRAM	Static random access memory
TSOP	Thin small outline package
WE	Write enable

Document Conventions

Units of Measure

Symbol	Unit of Measure			
ns	nano seconds			
V	Volts			
μA	micro Amperes			
mA	milli Amperes			
mV	milli Volts			
mW	milli Watts			
MHz	Mega Hertz			
pF	pico Farad			
°C	degree Celcius			
W	Watts			



Document History Page

Document Title: CY7C1041BN 256 K x 16 Static RAM Document Number: 001-06496					
Revision	ECN	Orig. of Change	Submission Date	Description of Change	
**	424111	NXR	See ECN	New Data Sheets	
*A	498575	NXR	See ECN	Added Automotive-A operating range updated Ordering Information Table	
*B	2897061	AJU	03/22/10	Removed obsolete parts from ordering information table Updated package diagrams	
*C	2906679	NXR	04/07/10	Removed inactive part CY7C1041BNL-20VXCT from the ordering information table.	
*D	3086674	PRAS	11/15/10	Removed inactive parts (CY7C1041BN-15ZXI, CY7C1041BN-15VXI). Added Ordering Code Definition.	
*E	3232637	PRAS	04/20/2011	Fixed unit for Input Load current and Output Leakage current under Electrical Characteristics table from mA to μA. Updated template. Added Units table.	

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